Acknowl agment Receipt

SUBMISSION TYPE: Information Disclosure Statement

APPLICATION NUMBER: 09687048

FIRST NAMED INVENTOR: Kuri-shi Lee

TITLE OF INVENTION: LEADFRAME AND SEMICONDUCTOR PACKAGE WITH IMPROVED

SOLDER JOINT STRENGTH

ATTORNEY DOCKET NUMBER: AMKOR-052A

FILE LISTING:

transmittal fee-transmittal fee-transmittal fee-transmittal tranIDS.xml 5346 Bytes
IDSfee.xml 2452 Bytes
u-feetra.dtd 38552 Bytes
e-feetra.xsl 15388 Bytes

us-information-disclosure-statement IDSids.xml 16117 Bytes us-information-disclosure-statement us-ids.dtd 11983 Bytes us-information-disclosure-statement e-idssta.xsl 17508 Bytes

EFS ID: 24714

FILE SIZE: 29368 Bytes

TIMESTAMP: Mon Mar 17 17:10:58 EST 2003
MESSAGE DIGEST: MpGX5uFlKcKafbVLgmVfTA==

DIGITAL CERTIFICATE HOLDER NAME: cn=Mark B. Garred, ou=Registered Attorneys

UPLOAD STATUS: You have successfully uploaded your submission to USPTO



TECHNOLOGY CENTER 2800

Htt 26 200



ELECTRONIC SUBMISSION OF LA AUTHORIZATION AMKOR-052A LEADFRAME AND SEMICONDUCTOR PACKAGE WITH OF The Property of the Propert

Docket Number:

Title:

Client:

Attachments:

By signing below, I authorize the electronic submission of the above-identified Information Disclosure Statement. I have reviewed the document and authorize a member of the support staff to affix an electronic signature on my behalf.

Mark B. Garred





ATTORNEY DOCKET NO: AMKOR-052A

ITLE: Leadframe and semiconductor package with improved solder joint strength

Certificate of Mailing under 37 CFR 1.8 or 37 CFR 1.10

以 I hereby certify that this correspondence is being deposited wit时the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:

Assistant Commissioner for Patents Washington, D.C. 20231

☐ I hereby certify that this correspondence is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10, Express Mail No. * addressed to:

PATENT APPLICATION ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

on March 17, 2003

(Signature)

Kristin West

(Typed name of person signing certificate)

Note: Each paper must have its own certificate of mailing, or this certificate must identify each submitted paper.

- 1. Certificate of Mailing;
- 2. Transmittal:
- 3. Information Disclosure Statement (2 pages);
- 4. Form PTO-1449 (in duplicate);
- 5. Copy of Acknowledgement Receipt, Transmittal, Fee Transmittal, and Electronic Submission of IDS Authorization; and
- 6. Return Receipt Postcard

Please type a plus sign (+) inside this box ——

/ 984 2816

PTO/SB/21 (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

				_
Application Number	09/687,048			
Filing Date	10/13/2000	ŤEC		
First Named Inventor	Tae Heon Lee	10:44		70
Group Art Unit	2814	001	:5 :>	C
Examiner Name	Nguyen, Dilinh P.	CEN	رن ادم:	3
Attorney Docket Number	AMKOR-052A	TER	ر تا دري م	7

Total Number of Pages In This Subm	Attorney Docket Number	AMKOR-052A \approx 22
	FNCLOSURES (check	(all that apply)
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request X Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53	Assignment Papers (for an Application) Drawing(s) Licensing-related Papers Petition Petition Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence Address Terminal Disclaimer Request for Refund CD, Number of CD(s) Remarks	After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter X Other Enclosure(s) (please identify below): Form PTO-1449; Disclosure documents listed on Form PTO-1449; Copy of Acknowledgement Receipt, Transmittals and Electronic Submission of IDS Authorization; and Return Receipt Postcard
SIGNATU	I IRE OF APPLICANT, ATTORNEY, OR	AGENT
Firm or Mark B. Garred STETINA BIRL Signature Date 31703	NDA GARRED & BRUCKER	
	CERTIFICATE OF MAILING	

CERTIFICATE OF MAILING					
	pondence is being deposited with the U to: Commissioner for Patents, Washin			first class	
Typed or printed name	Kristin West				
Signature	Minotin West	Date	3-17-03		

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.



TRANSMITTAL FORM

Electronic Version 1.0.3

Stylesheet Version: 1.0

Submission Type: Information

Disclosure Statement

Application Number:

09/687,048

Attorney Docket

AMKOR-

Number:



LEADFRAME AND SEMICONDUCT@R PACKAGE WITH IMPROVED SOLDER JOINT STRENGTH

First Named Inventor: Kuri-shi Tae Heon Lee

SUBMITTED BY

Name:

Mark B. Garred

Registration Number:

34,823

Electronic Signature Mark: /mbg/

Date Signed: 20030317

I certify that the use of this system is for OFFICIAL correspondence between patent applicants or their representatives and the USPTO. Fraudulent or other use besides the filing of official correspondence by authorized parties is strictly prohibited, and subject to a fine and/or imprisonment under applicable law.

I, the undersigned, certify that I have viewed a display of document(s) being electronically submitted to the United States Patent and Trademark Office, using either the USPTO provided style sheet or software, and that this is the document(s) I intend for initiation or further prosecution of a patent application noted in the submission. This document(s) will become part of the official electronic record at the USPTO.

Attached Files:

us-information-disclosure-statement

IDSids.xml

fee-transmittal

IDSfee.xml

Comments:





Electronic Version 1.1.2

Stylesheet Version: 1.0

Patent fees are subject to annual revisions on or about October 1st of each year.

Large Entity

TOTAL FEES AUTHORIZED: \$ 180

The commissioner is hereby authorized to charge indicated processing and/or publication fees and credit any overpayments to:

Deposit Account Number:

19-4330

19-4330

Deposit Account Name:

STETINA BRUNDA GARRED & BRUCKER

SUBMITTED BY

Authorized Name:

Mark B. Garred

Electronic Signature Mark:

/mbg/

Date Signed:

20030313

ADDITIONAL FEES

Fee Description	Number	Quantity	Fee Code	Amount	Fee Paid
Submission Of Information Disclosure Stmt Fee		1	1806	\$ 180	\$ 180

Subtotal For Additional Fees: \$ 180

TECHNOLOGY CENTER 2800

MANUFACTURE OF SEMICONDUCTOR DEVICE

Patent Number:

JP10256240

Publication date:

1998-09-25

Inventor(s):

FUKAZAWA MASANAGA;; KADOMURA SHINGO;; FUKUDA

Applicant(s):

SONY CORP

Requested Patent:

☐ JP10256240

Application

JP19970158570 19970616

Priority Number(s):

IPC Classification:

H01L21/3065; H01L21/768

EC Classification:

Equivalents:

Abstract

PROBLEM TO BE SOLVED: To form a connection hole in an interlayer insulating film by a dry etching process, using not only a general composition etching gas but also an etching gas containing no fluorocarbon-loosed gas.

SOLUTION: This method for manufacturing a semiconductor device includes a step of forming a connection hole 14 in an inter-layer insulating film by a dry etching process using an etching gas. In this case, a film 12 having a low dielectric constant is an insulating film which is made of a compound, having SiF or CF couplings in a chemical structural formula. Specifically, the compound may be SiOF, cyclic fluororesin siloxane copolymer or polyfluoroaryl ether. When such an insulating film employed, active species of F- or fluoroacrbon- boased moleules emitted from inside of the connection hole 24 of the inter-layer insulating film can cause an etching rate of the insulating film inside the hole 14 to be increased.

Data supplied from the **esp@cenet** database - I2

* NOTICES *

Japan Patent Office is not responsible for any damages caused by the use of this translation.

- 1. This document has been translated by computer. So the translation may not reflect the original precisely.
- 2. **** shows the word which can not be translated.
- 3.In the drawings, any words are not translated.

CLAIMS

[Claim(s)]

[Claim 1] the layer insulation film which consists of a compound which has SiF combination or CF combination in a chemical structure formula by the dry etching using etching gas -- connection -- the manufacture method of the semiconductor device characterized by having the process which forms a hole

[Claim 2] The compound which has SiF combination or CF combination in a chemical structure formula is the manufacture method of the semiconductor device according to claim 1 characterized by the ranges of specific inductive capacity being 1-4.

[Claim 3] the compound which has SiF combination or CF combination in a chemical structure formula -- under etching -- connection of a layer insulation film -- a hole -- the active species of the molecule of F emitted from inside, or a fluorocarbon system -- connection -- a hole -- the manufacture method of the semiconductor device according to claim 1 characterized by including F beyond the grade which can be made to accelerate etching of an inner insulator layer

* NOTICES *

Japan Patent Office is not responsible for any damages caused by the use of this translation.

- 1. This document has been translated by computer. So the translation may not reflect the original precisely.
- 2.**** shows the word which can not be translated.
- 3.In the drawings, any words are not translated.

DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] the connection formed in the layer insulation film according to the example of this invention -- it is the outline cross section showing a hole

[Drawing 2] It is the outline cross section showing the structure of the sample used for the example of this invention.

[Drawing 3] the connection which tried to form in the layer insulation film used for comparison with the example of this invention -- it is the outline cross section showing a hole

[Description of Notations]

10 Si Substrate and 11 SiO2 Layer and 12 Low Dielectric Constant Film and 13 Photoresist and 14 Connection -- Hole

[Translation done.]